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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroshi SERA

Group Art Unit: 2813

Application No.: 10/826,366

Examiner: C. RODGERS

Filed: April 19, 2004

Docket No.: 119209

For: METHOD FOR MAKING THIN-FILM SEMICONDUCTOR DEVICE, THIN-FILM SEMICONDUCTOR DEVICE, METHOD FOR MAKING ELECTRO-OPTIC APPARATUS, ELECTRO-OPTIC APPARATUS, AND ELECTRONIC APPARATUSES

REQUEST FOR RECONSIDERATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In reply to the May 15, 2007 Office Action, reconsideration of the rejections is respectfully requested in light of the following remarks.

Claims 1-6 and 8-12 are pending in this application. The Office Action rejects claims 1-4, 6 and 8-12 under 35 U.S.C. §103(a) over U.S. Patent Application Publication No. 2002/0145142 to Chen et al. ("Chen") in view of U.S. Patent No. 6,930,326 to Kato et al. ("Kato"), and rejects claim 5 under 35 U.S.C. §103(a) over Chen in view of Kato and further in view of U.S. Patent No. 5,576,230 to Guldi. These rejections are respectfully traversed.

The Office Action now asserts, contrary to the previous indication of allowability and analysis of Chen set forth in the March 8, 2007 Office Action, that Chen allegedly discloses forming a gate-insulating film 34 on the semiconductor film 32, the gate-insulating film being composed of silicone oxide. The Office Action refers to, for example, claim 13 of Chen for